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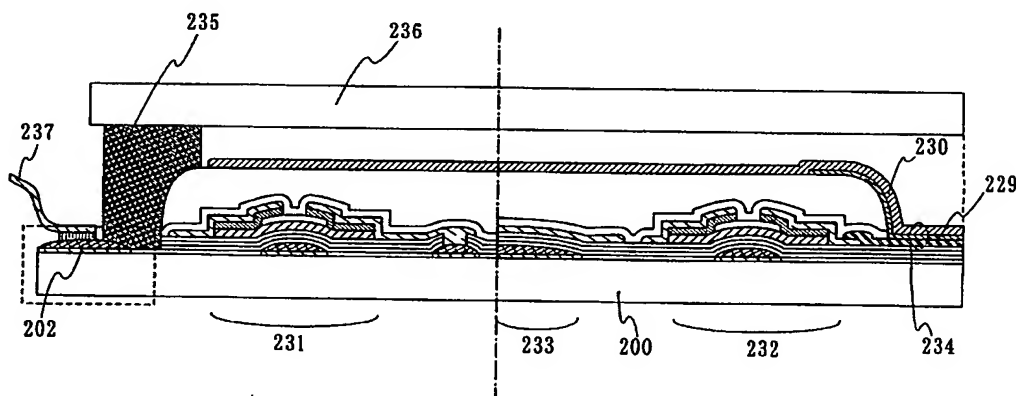
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(54) Title: DISPLAY DEVICE AND METHOD FOR MANUFACTURING THE SAME, AND TELEVISION RECEIVER



(57) Abstract: According to the present invention, which is a display device in which a light-emitting element where an organic substance generating luminescence referred to as electroluminescence or a medium including a mixture of an organic substance and an inorganic substance is sandwiched between electrodes is connected to a TFT, the invention is to manufacture a display panel by forming at least one or more of a conductive layer which forms a wiring or an electrode and a pattern necessary for manufacturing a display panel such as a mask layer for forming a predetermined pattern is formed by a method capable of selectively forming a pattern. A droplet discharge method capable of forming a predetermined pattern by selectively discharging a droplet of a composition in accordance with a particular object and by forming a conductive layer or an insulating layer is used as a method capable of selectively forming a pattern.

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